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August 2015

MOC205M, MOC206M, MOC207M, MOC211M, MOC212M, MOC213M, MOC216M, MOC217M 8-pin SOIC Single-Channel Phototransistor Output Optocoupler

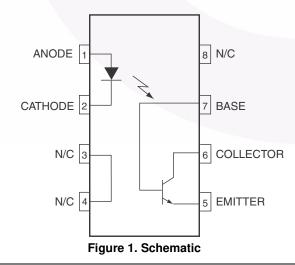
Features

- Closely Matched Current Transfer Ratios
- Minimum BV_{CEO} of 70 V Guaranteed
- MOC205M, MOC206M, MOC207M
- Minimum BV_{CEO} of 30 V Guaranteed
 - MOC211M, MOC212M, MOC213M, MOC216M, MOC217M
- Low LED Input Current Required for Easier Logic Interfacing
 - MOC216M, MOC217M
- Convenient Plastic SOIC-8 Surface Mountable Package Style, with 0.050" Lead Spacing
- Safety and Regulatory Approvals:
 - UL1577, 2,500 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 565 V Peak Working Insulation Voltage

Applications

- Feedback Control Circuits
- Interfacing and Coupling Systems of Different Potentials and Impedances
- General Purpose Switching Circuits
- Monitor and Detection Circuits

Schematic



Description

These devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector, in a surface mountable, small outline, plastic package. They are ideally suited for high-density applications, and eliminate the need for through-the-board mounting.

Package Outline

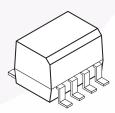


Figure 2. Package Outline

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–III
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	904	V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$, 100% Production Test with $t_m = 1$ s, Partial Discharge < 5 pC	1060	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	565	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	4000	V _{peak}
	External Creepage	≥ 4	mm
	External Clearance	≥ 4	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
Τ _S	Case Temperature ⁽¹⁾	150	°C
I _{S,INPUT}	Input Current ⁽¹⁾	200	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	300	mW
R _{IO}	Insulation Resistance at T _S , $V_{IO} = 500 V^{(1)}$	> 10 ⁹	Ω

Note:

1. Safety limit values - maximum values allowed in the event of a failure.

Absolute Maximum Ratings

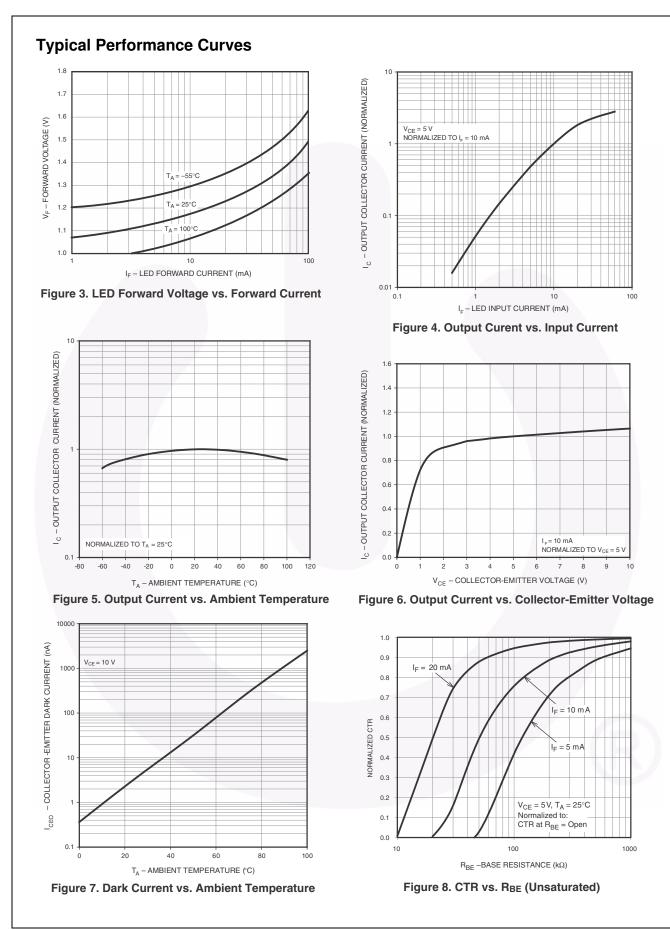
Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A = 25^{\circ}C$ unless otherwise specified.

Symbol	Rating	Value	Unit
TOTAL DEVI	CE		
T _{STG}	Storage Temperature	-40 to +125	°C
T _A	Ambient Operating Temperature	-40 to +100	°C
Т _Ј	Junction Temperature	-40 to +125	°C
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C
Р	Total Device Power Dissipation @ T _A = 25°C	240	mW
PD	Derate above 25°C	2.94	mW/°C
EMITTER			
I _F	Continuous Forward Current	60	mA
I _F (pk)	Forward Current – Peak (PW = 100 µs, 120 pps)	1.0	А
V _R	Reverse Voltage	6.0	V
Р	LED Power Dissipation @ $T_A = 25^{\circ}C$	90	mW
PD	Derate above 25°C	0.8	mW/°C
DETECTOR			
۱ _C	Continuous Collector Current	150	mA
V _{CEO}	Collector-Emitter Voltage	30	V
V _{ECO}	Emitter-Collector Voltage	7	V
Р	Detector Power Dissipation @ T _A = 25°C	150	mW
P_D	Derate above 25°C	1.76	mW/°C

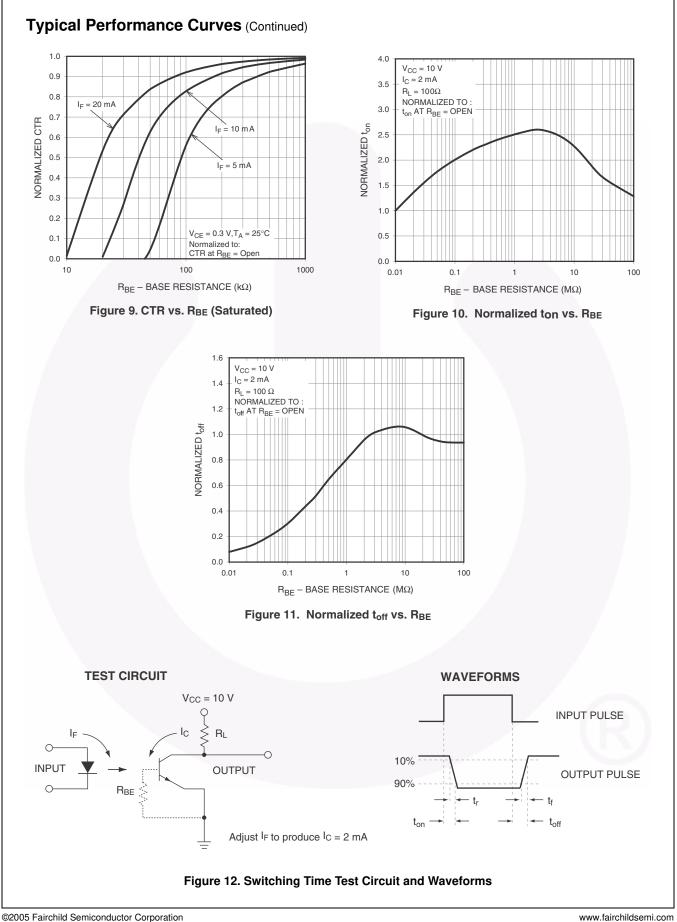
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
EMITTER		1			11	
	Input Forward Voltage					
V _F	MOC216M, MOC217M	$I_F = 1 \text{ mA}$		1.07	1.3	V
	MOC205M, MOC206M, MOC207M MOC211M, MOC212M, MOC213M	I _F = 10 mA		1.15	1.5	V
I _R	Reverse Leakage Current	V _R = 6 V		0.001	100	μA
C _{IN}	Input Capacitance			18		pF
DETECTO	DR III					
I _{CEO1}	Collector Erzitter Dark Current	$V_{CE} = 10 \text{ V}, \text{ T}_{A} = 25^{\circ}\text{C}$		1.0	50	nA
I _{CEO2}	Collector-Emitter Dark Current	V _{CE} = 10 V, T _A = 100°C		1.0		μA
	Collector-Emitter Breakdown Voltage					
BV _{CEO}	MOC205M, MOC206M, MOC207M	I _C = 100 μA	70	100		V
DICEO	MOC211M, MOC212M, MOC213M, MOC216M, MOC217M	I _C = 100 μA	30	100		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 10 μA	70	120		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 100 μA	7	10		V
C _{CE}	Collector-Emitter Capacitance	f = 1.0 MHz, V _{CE} = 0		7		pF
COUPLED)		•		•	
	Collector-Output Current					
	MOC205M	I _F = 10 mA, V _{CE} = 10 V	40		80	%
	MOC206M	I _F = 10 mA, V _{CE} = 10 V	63		125	%
	MOC207M	I _F = 10 mA, V _{CE} = 10 V	100		200	%
CTR	MOC211M	I _F = 10 mA, V _{CE} = 10 V	20			%
	MOC212M	I _F = 10 mA, V _{CE} = 10 V	50			%
	MOC213M	I _F = 10 mA, V _{CE} = 10 V	100	8		%
	MOC216M	I _F = 1 mA, V _{CE} = 5 V	50			%
	MOC217M	I _F = 1 mA, V _{CE} = 5 V	100			%
	Collector-Emitter Saturation Voltage					
V _{CE(SAT)}	MOC205M, MOC206M, MOC207M MOC211M, MOC212M, MOC213M	I _C = 2 mA, I _F = 10 mA			0.4	V
	MOC216M, MOC217M	I _C = 100 μA, I _F = 1 mA			0.4	V
t _{on}	Turn-On Time	$I_{C} = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ R _L = 100 Ω (Figure 12)		7.5		μs
t _{off}	Turn-Off Time	$I_{C} = 2 \text{ mA}, V_{CC} = 10 \text{ V}, R_{L} = 100 \Omega \text{ (Figure 12)}$		5.7		μs
t _r	Rise Time	$\label{eq:lc} \begin{array}{l} I_C = 2 \text{ mA}, \ V_{CC} = 10 \text{ V}, \\ R_L = 100 \ \Omega \ (\text{Figure 12}) \end{array}$		3.2		μs
t _f	Fall Time	$I_{C} = 2 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_{L} = 100 \Omega$ (Figure 12)		4.7		μs

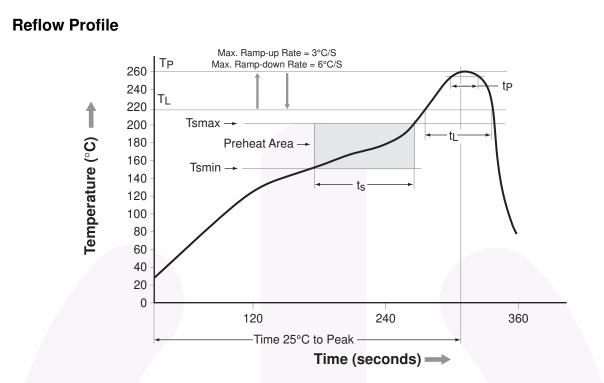
Electrical Characteristics

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MOC20xM, MOC21xM — 8-pin SOIC Single-Channel Phototransistor Output Optocoupler





Profile Freature	ofile Freature Pb-Free Assembly Profile	
Temperature Minimum (Tsmin)	150°C	
Temperature Maximum (Tsmax)	200°C	
Time (t _S) from (Tsmin to Tsmax)	60–120 seconds	
Ramp-up Rate (t _L to t _P)	3°C/second maximum	
Liquidous Temperature (T _L)	217°C	
Time (t_L) Maintained Above (T_L)	60–150 seconds	
Peak Body Package Temperature	260°C +0°C / -5°C	
Time (t _P) within 5°C of 260°C	30 seconds	
Ramp-down Rate $(T_P \text{ to } T_L)$	6°C/second maximum	
Time 25°C to Peak Temperature	8 minutes maximum	

Ordering Information⁽²⁾

Part Number	Package	Packing Method
MOC205M	Small Outline 8-Pin	Tube (100 Units)
MOC205R2M	Small Outline 8-Pin	Tape and Reel (2500 Units)
MOC205VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	Tube (100 Units)
MOC205R2VM	Small Outline 8-Pin, DIN EN/IEC60747-5-5 Option	Tape and Reel (2500 Units)

Note:

2. The product orderable part number system listed in this table also applies to the MOC20XM and MOC21XM products.

Marking Information

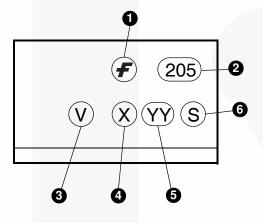
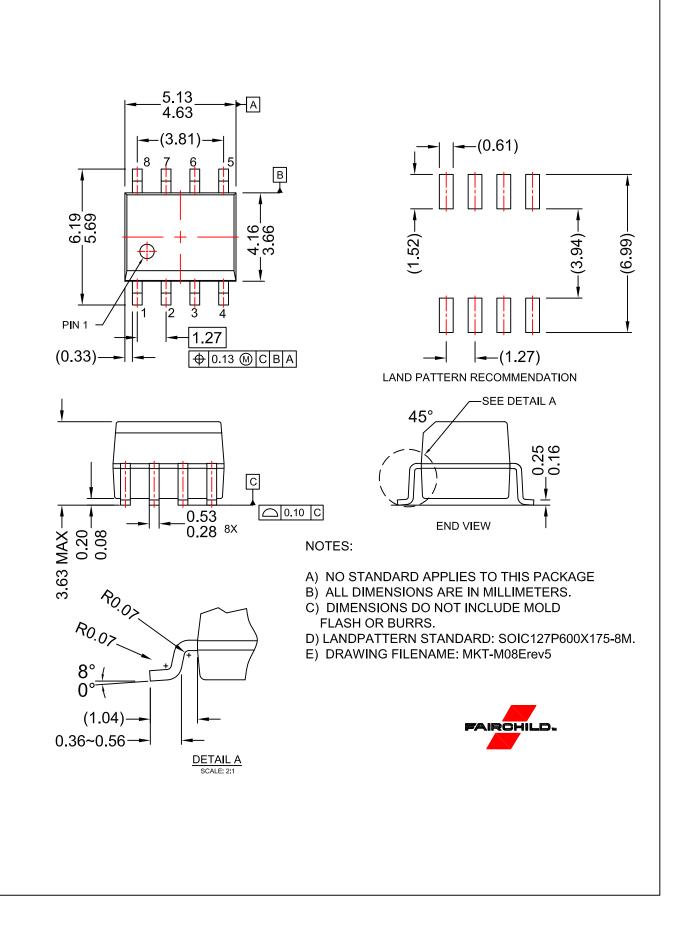


Figure 14. Top Mark

Table 1. Top Mark Definitions

1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "4"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code



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